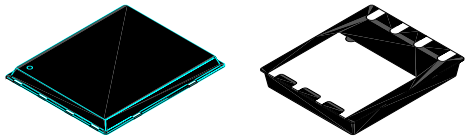
STL60NH3LL

N-channel 30V - 0.0065Ω - 30A - PowerFLAT™ (6x5) Ultra low gate charge STripFET™ Power MOSFET

General features

Type	V_{DSS}	$R_{DS(on)}$	I_D
STL60NH3LL	30V	<0.0085Ω	16A (2)

- Improved die-to-footprint ratio
- Very low profile package (1mm max)
- Very low thermal resistance
- Very low gate charge
- Low threshold device

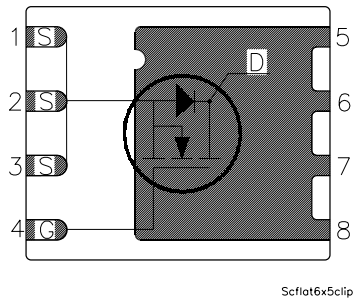


PowerFLAT™(6x5)

Description

This application specific Power MOSFET is the latest generation of STMicroelectronics unique "STripFET™" technology. The resulting transistor is optimized for low on-resistance and minimal gate charge. The Chip-scaled PowerFLAT™ package allows a significant board space saving, still boosting the performance.

Internal schematic diagram



Applications

- Switching application

Order codes

Part number	Marking	Package	Packaging
STL60NH3LL	L60NH3LL	PowerFLAT™ (6 x 5)	Tape & reel

Contents

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	30	V
V_{GS}	Gate-source voltage	± 16	V
I_D (1)	Drain current (continuous) at T_C = 25°C	30	A
I_D (1)	Drain current (continuous) at T_C = 100°C	30	A
I_D(2)	Drain current (continuous) at T_C = 25°C	16	A
I_{DM} (3)	Drain current (pulsed)	64	A
P_{TOT}(1)	Total dissipation at T_C = 25°C	60	W
P_{TOT}(2)	Total dissipation at T_C = 25°C	4	W
	Derating factor	0.03	W/°C
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 150	°C

1. The value is rated according $R_{thj\text{-}C}$ and is limited by wire bonding.
2. This value is according $R_{thj\text{-}pcb}$
3. Pulse width limited by safe operating area

Table 2. Thermal resistance

Symbol	Parameter	Value	Unit
Rthj-case	Thermal resistance junction-case (drain) Max	2.08	°C/W
Rthj-pcb (1)	Thermal resistance junction-pcb Max	31.3	°C/W

1. When mounted on FR-4 board of 1inch^2, 2 oz Cu, t<10sec

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test condictions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 250µA, V_{GS}= 0	30			V
I_{DSS}	Zero gate voltage drain current (V_{GS} = 0)	V_{DS} = Max rating, V_{DS} = Max rating,@125°C			1 10	µA µA
I_{GSS}	Gate body leakage current (V_{DS} = 0)	V_{DS} = ± 16V			±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS}= V_{GS}, I_D = 250µA	1			V
$R_{DS(on)}$	Static drain-source on resistance	V_{GS}= 10V, I_D= 8A V_{GS}= 4.5V, I_D= 8A		0.0065 0.0075	0.0085 0.0105	Ω Ω

Table 4. Dynamic

Symbol	Parameter	Test condictions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS}=25V, f = 1MHz, V_{GS}=0		1810 565 41		pF pF pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 15V, I_D = 16A, V_{GS} = 4.5V (see Figure 15)		18 4.8 5.3	24	nC nC nC
R_G	Gate input resistance	f=1 MHz Gate DC Bias = 0 Test signal level = 20mV open drain	0.5	1.5	3	Ω

Table 5. Switching times

Symbol	Parameter	Test condictions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	V_{DD} = 15V, I_D = 8A R_G= 4.7Ω, V_{GS}= 10V, (see Figure 14)		8 65		ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	V_{DD} = 15V, I_D = 8A R_G= 4.7Ω, V_{GS}= 10V, (see Figure 14)		30 20		ns ns

Table 6. Source drain diode

Symbol	Parameter	Test condictions	Min	Typ.	Max	Unit
I_{SD} I_{SDM}	Source-drain current Source-drain current (pulsed)				16 64	A A
V_{SD} (1)	Forward on voltage	I_{SD} = 16A, V_{GS} = 0			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 16V, di/dt = 100A/µs V_{DD} = 20V, T_j = 25°C (see Figure 16)		22 32 1.9		ns nC A

1. Pulsed: Pulse duration = 300µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

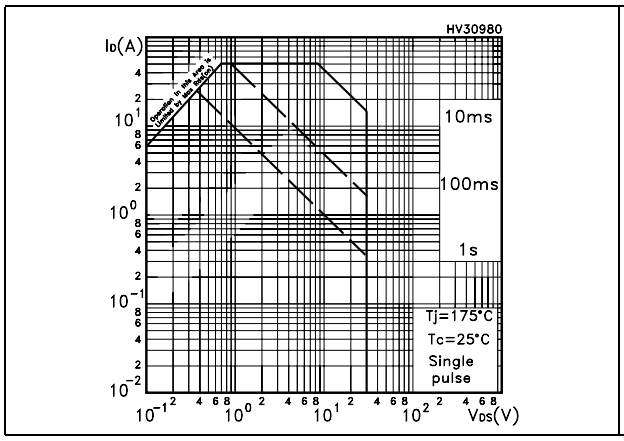


Figure 2. Thermal impedance

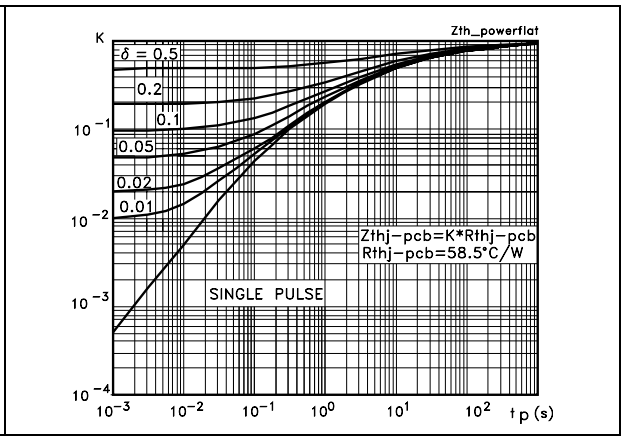


Figure 3. Output characterisics

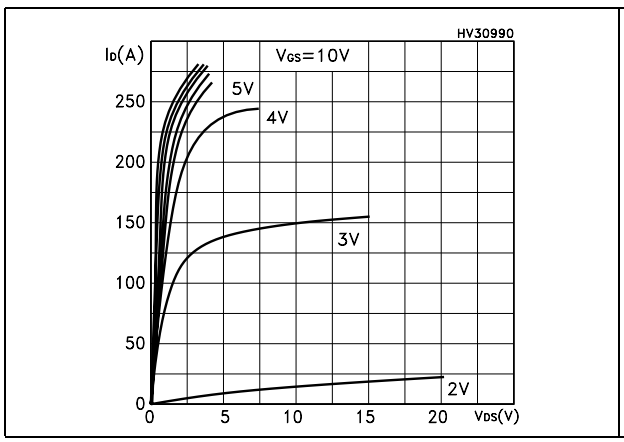


Figure 4. Transfer characteristics

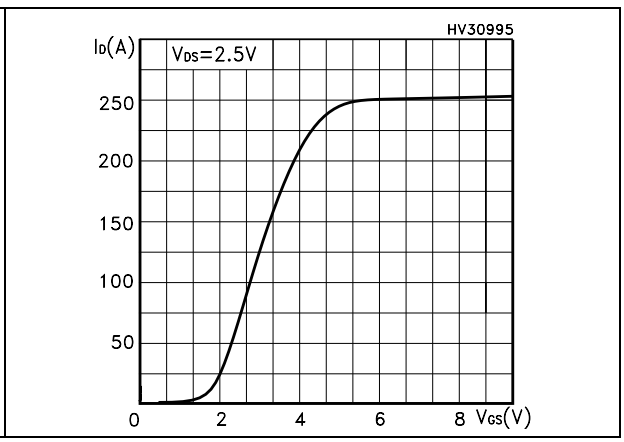


Figure 5. Normalized B_{VDSS} vs temperature

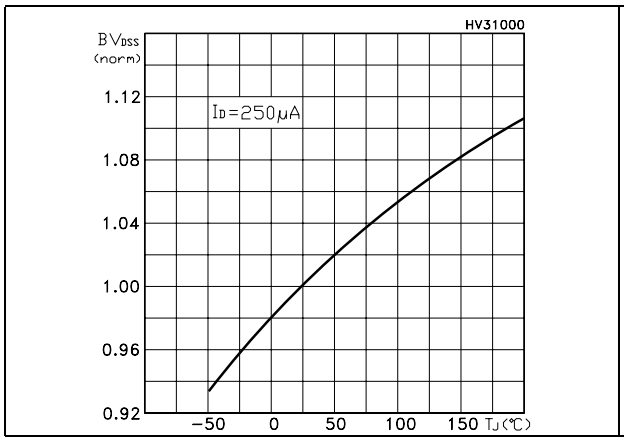


Figure 6. Static drain-source on resistance

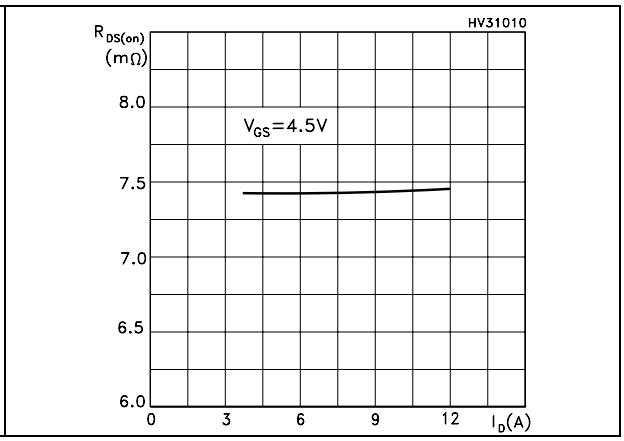


Figure 7. Gate charge vs gate-source voltage

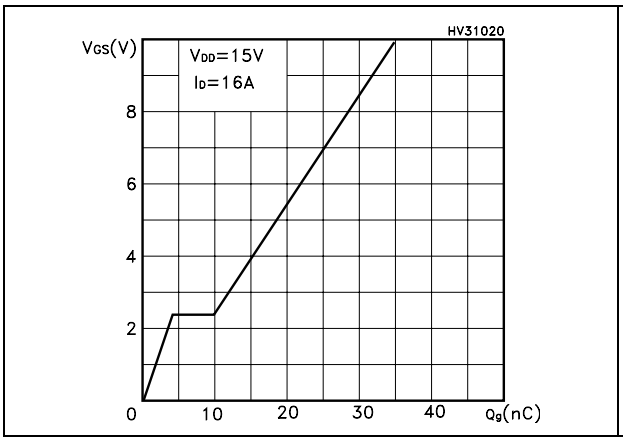


Figure 8. Capacitance variations

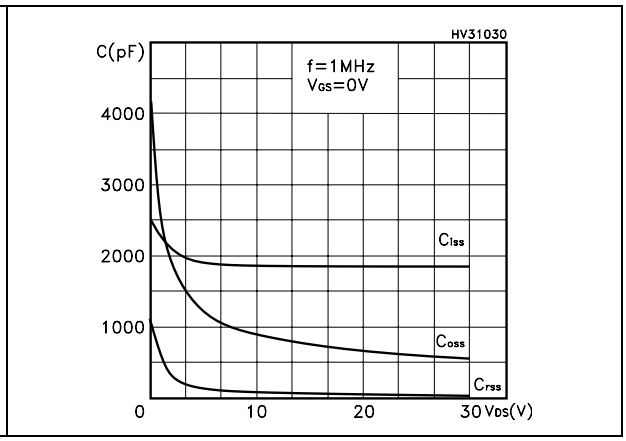


Figure 9. Normalized gate threshold voltage vs temperature

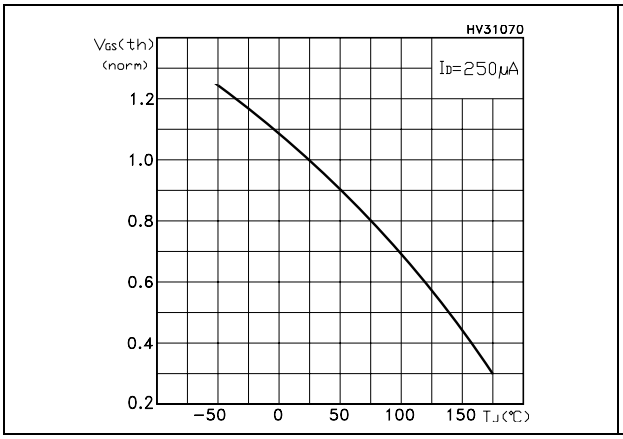


Figure 10. Normalized on resistance vs temperature

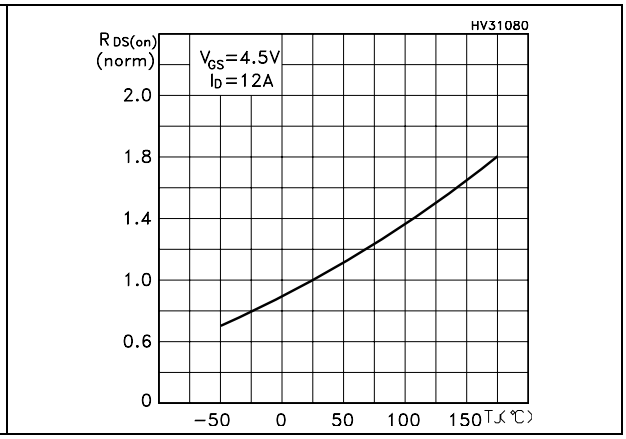


Figure 11. Source-drain diode forward characteristics

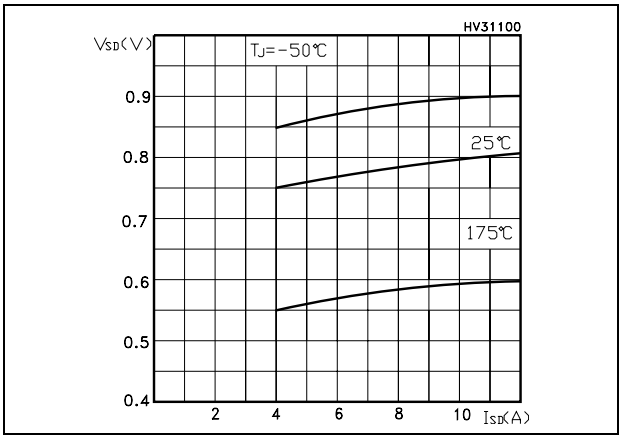


Figure 12. Allowable Iav vs Time in Avalanche

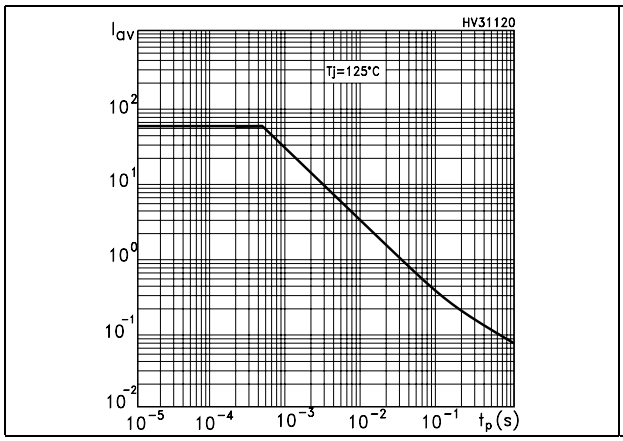
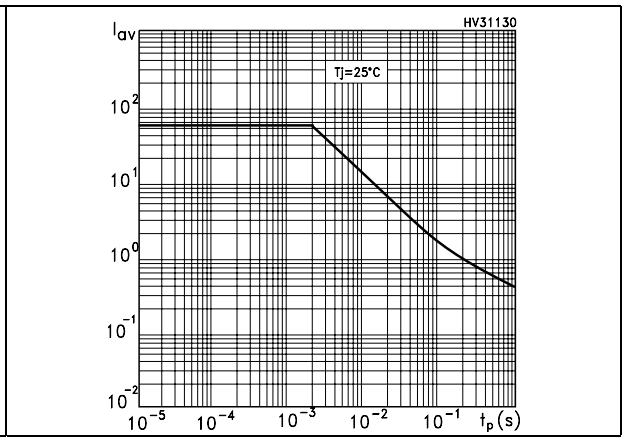


Figure 13. Allowable Iav vs Time in Avalanche



The previous curve gives the single pulse safe operating area for unclamped inductive loads under the following conditions:

$P_{D(AVE)} = 0.5*(1.3*BV_{DSS} *I_{AV})$

$E_{AS(AR)} = P_{D(AVE)} *t_{AV}$

Where:

I_{AV} is the allowable current in avalanche

$P_{D(AVE)}$ is the average power dissipation in avalanche (single pulse)

t_{AV} is the time in avalanche

3 Test circuit

Figure 14. Switching times test circuit for resistive load

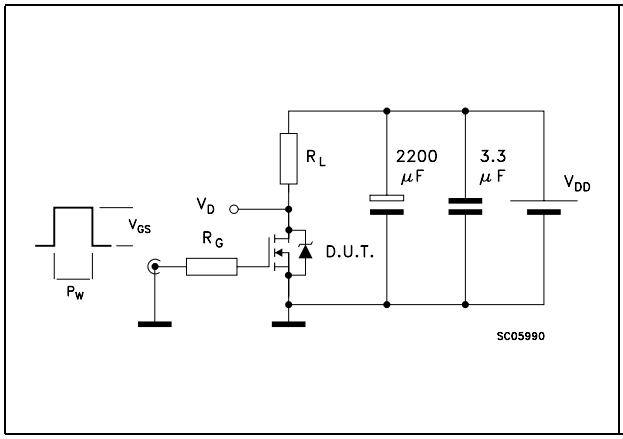


Figure 15. Gate charge test circuit

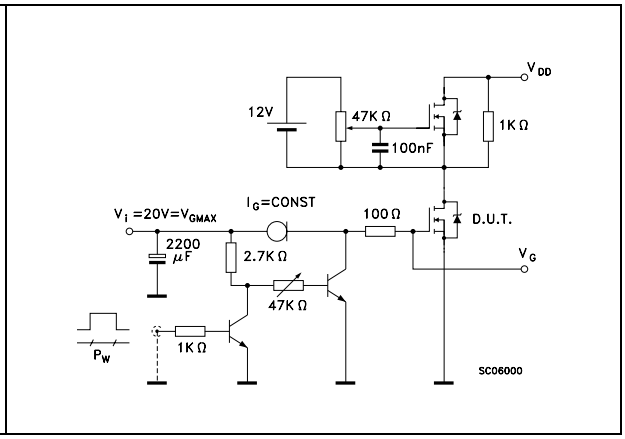


Figure 16. Test circuit for inductive load switching and diode recovery times

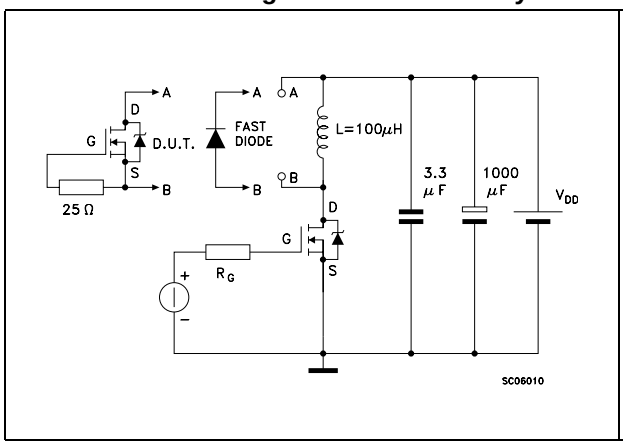


Figure 17. Unclamped inductive load test circuit

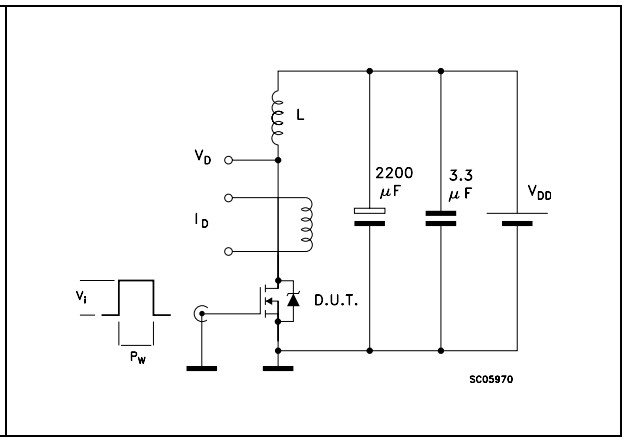


Figure 18. Unclamped inductive waveform

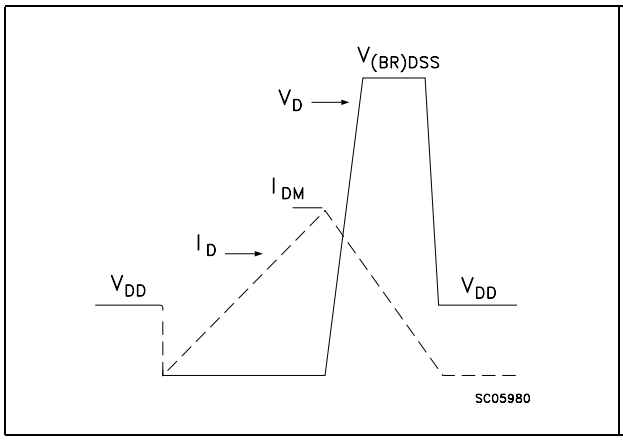
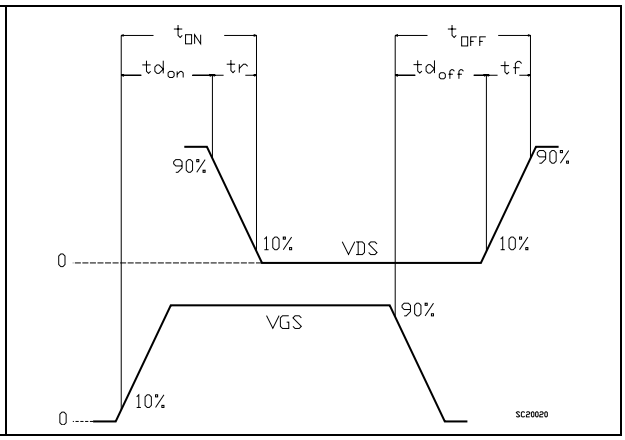


Figure 19. Switching time waveform

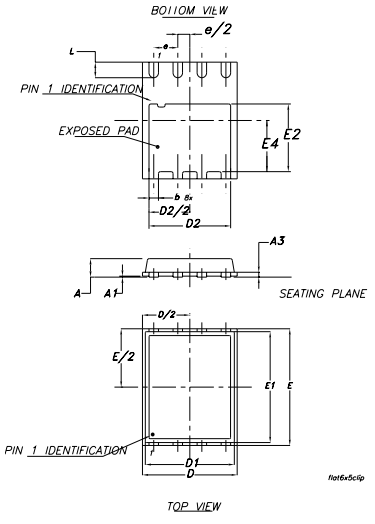


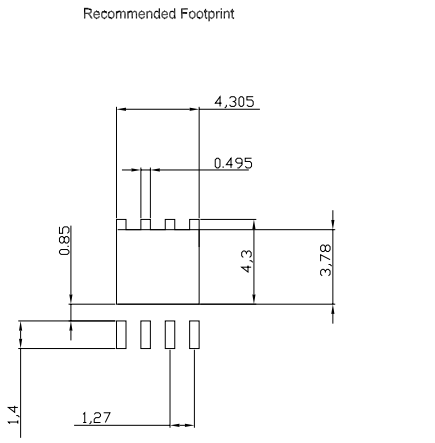
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

PowerFLAT™ (6x5) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	0.80	0.83	0.93	0.031	0.032	0.036
A1		0.02	0.05		0.0007	0.0019
A3		0.20			0.007	
b	0.35	0.40	0.47	0.013	0.015	0.018
D		5.00			0.196	
D1		4.75			0.187	
D2	4.15	4.20	4.25	0.163	0.165	0.167
E		6.00			0.236	
E1		5.75			0.226	
E2	3.43	3.48	3.53	0.135	0.137	0.139
E4	2.58	2.63	2.68		0.103	0.105
e		1.27			0.050	
L	0.70	0.80	0.90	0.027	0.031	0.035





Note: all dimentions are in mm.

5 Revision history

Table 7. Revision history

Date	Revision	Changes
21-Jul-2004	1	First Release
05-Oct-2004	2	Values Changed
12-Apr-2006	3	New template

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